ANGELTECH
CS INTERNATIONAL CONFERENCE

DISCO

Total solutions for Silicon Carbide from wafer making to device making

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Gerald Klug
General Sales Manager
DISCO HI-TEC EUROPE GmbH

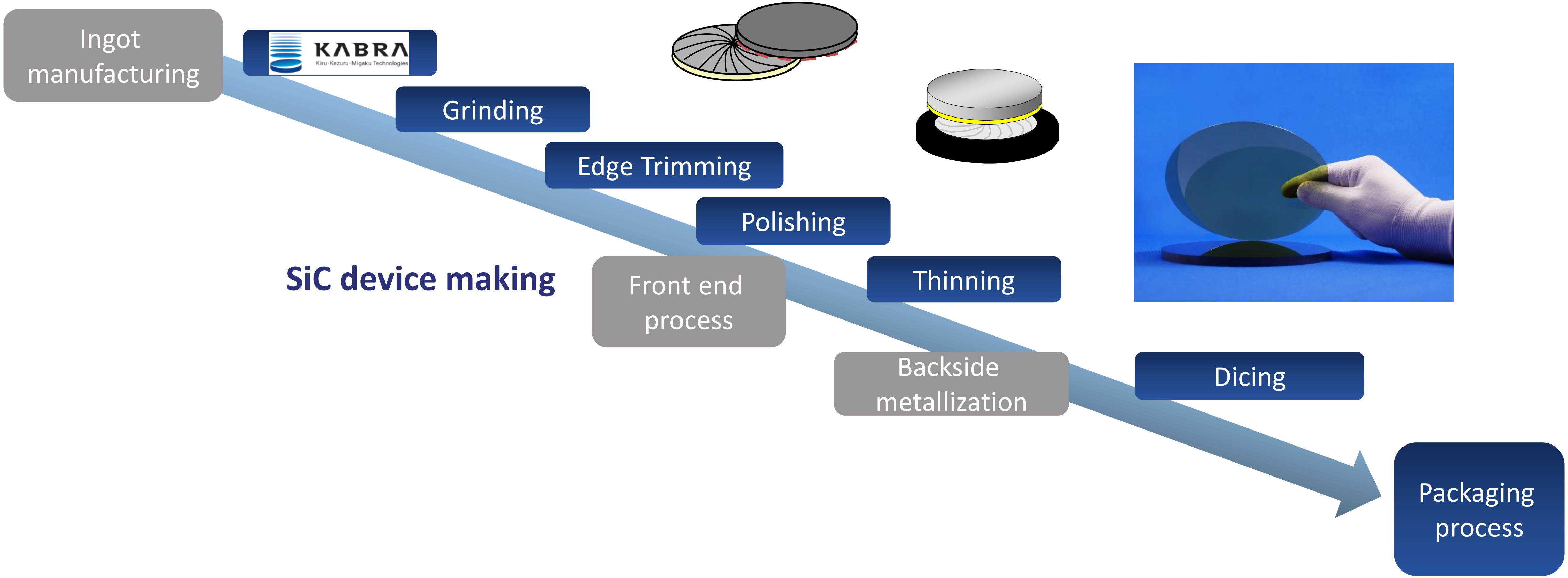
Table of contents

DISCO

1. Introduction
2. Solution for SiC wafer making
3. Advantages of KABRA®
4. Solution for SiC device making – Thinning
5. Solution for SiC device making – Dicing
6. DFL7562 Type-D – Laser full cut
7. Laser full cut of thin Silicon
8. Laser full cut of SiC

Introduction

- DISCO provides various solutions for SiC wafer making & device making



SiC wafer making

Ingot manufacturing

KABRA

Kiru·Kezuru·Migaku Technologies

Grinding

Edge Trimming

Polishing

SiC device making

Front end process

Thinning

Backside metallization

Dicing

Packaging process

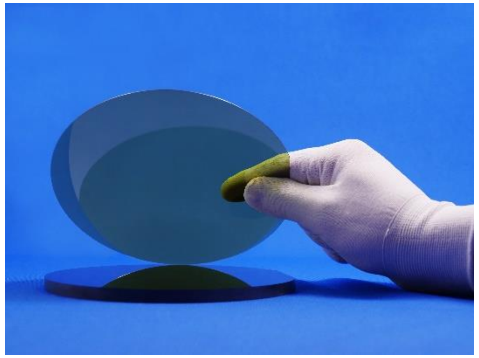
Solution for SiC wafer making

- The new generation of SiC wafer production by high-speed ingot slicing

Fully Automatic KABRA® System KABRA!zen

Φ8-inch ingot processing

Support a maximum ingot thickness of 40 mm



Grinding

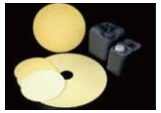
Fully automatic high-precision grinder

DFG8640

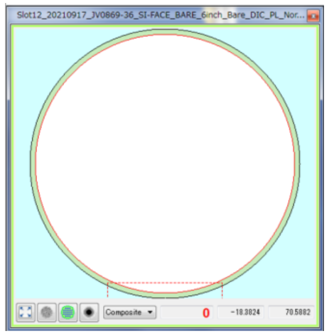
Polishing

Full-auto polisher (CMP)

DFP8141 with E Pad



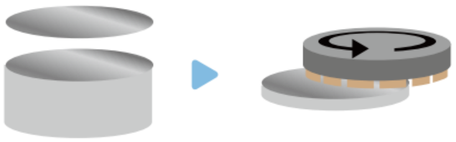
No scratch



Advantages of KABRA®

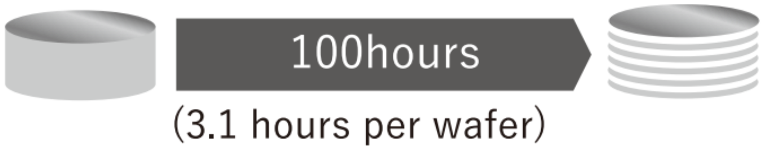
Existing process

KABRA process



- **Processing time is greatly reduced**

Existing process



(3.1 hours per wafer)

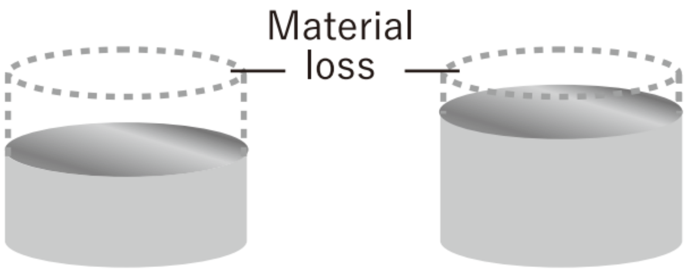
KABRA process

(10minutes per wafer)

- **Lapping process is no longer required**

Existing process

KABRA process



KABRA
Kiru·Kezuru·Migaku Technologies

- **Number of wafers produced increases 1.4 times more than that of existing processes**

Contact us

Some slides are not available for distribution,
but we are happy to discuss individually.

DISCO HI-TEC EUROPE GmbH
Liebigstr. 8, 85551 Kirchheim b. München, GERMANY

Tel: +49 (0)89 90903 0
E-Mail: contactsales@discoeurope.com

Websites:
https://www.discoeurope.com
https://www.dicing-grinding.com/